

## Supporting Information

to

### In-situ Photo-Induced Chemical Doping of Solution-Processed Graphene Oxide for Electronic Applications

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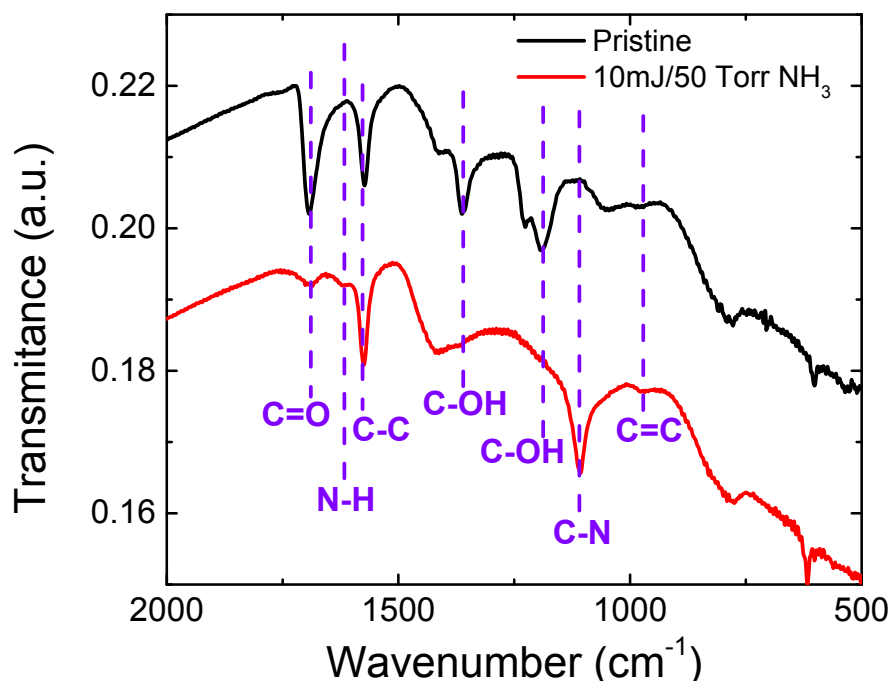
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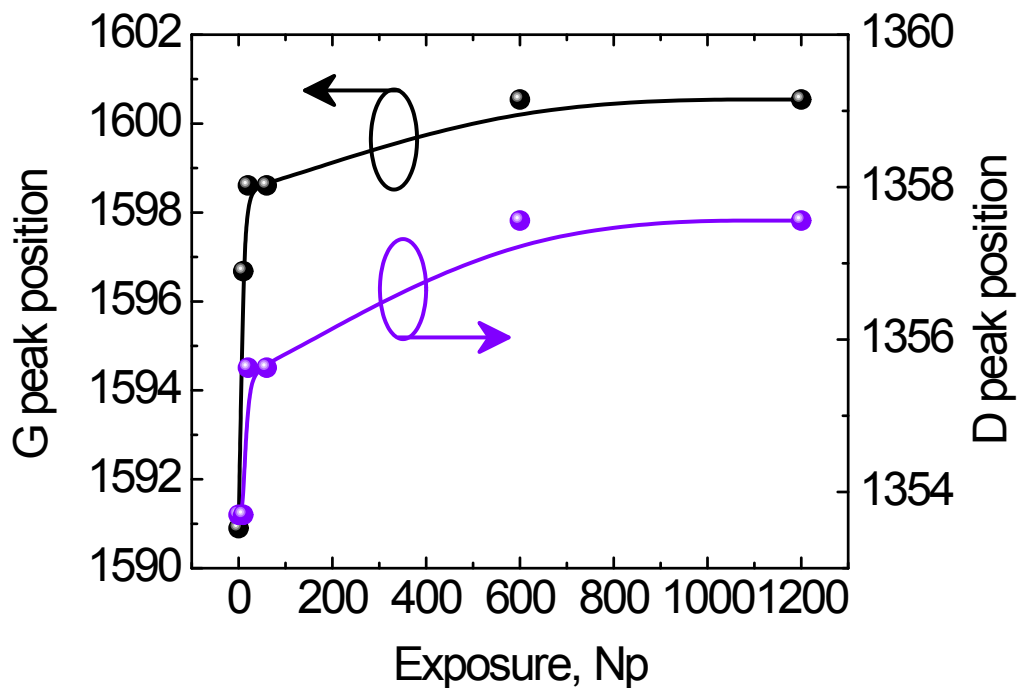
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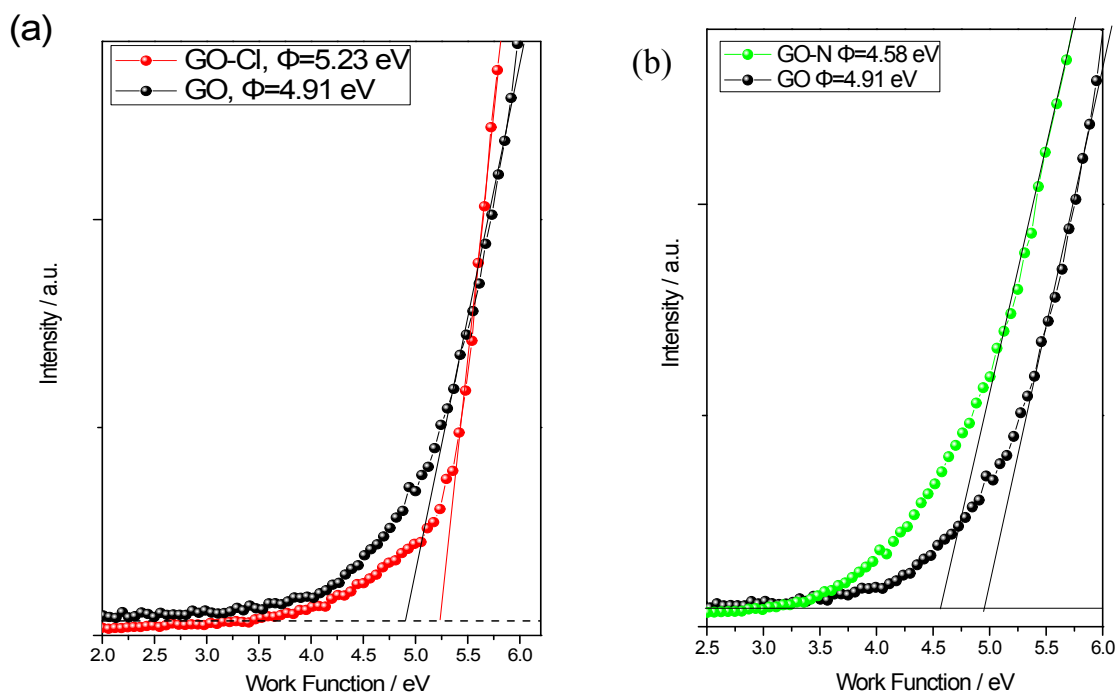
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**Figure S1:** FTIR spectra of GO sheets before (pristine) and after irradiation with 10 laser pulses in 50 Torr NH<sub>3</sub>;



**Figure S2:** Dependence of the D and G bands positions on number of laser pulses,  $N_p$ .



**Figure S3:** UPS spectra of GO films before (pristine) and after irradiation with 10 laser pulses in 50 Torr  $\text{Cl}_2$  (a) and  $\text{NH}_3$  (b).